

N-Channel 100V MOSFET

E100N1P5OH1

V _{DS} (V)	$R_{DS(on),max}$ (m Ω)	I _D (A)
100V	1.5 @ V _{GS} = 10V	330

Features

- Low R_{DS(on)} trench technology
- Low thermal impedance
- Fast switching speed
- 100% avalanche tested

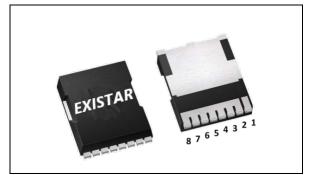
Applications

- DC/DC conversion
- Power switch
- Moto driver

Package And Ordering Information

Ordering code	Package	Marking
E100N1P5OH1	TOLL-8	E100N1P5OH1

TOLL-8





Package	Units/ Reel	Reels/ Inner Box	Units/ Inner Box
TOLL-8	2000	1	2000

Key Performance Parameters

Parameter	Value	Unit
VDS, min @ Tj(max)	100	V
ID, pulse	1300	А
RDS(ON), max @ VGS=10V	1.5	mΩ
Qg	258	nC

Absolute Maximum Ratings at Tj=25°C Unless Otherwise Noted

Parameter	Symbol	Limit	Unit	
Drain-source voltage	V _{DS}	100		
Gate-source voltage	V_{GS}	±20	V	
Tc=25°C			330	
Continuous drain current	T _C =100°C	- I _D	252	
Pulsed drain current		I _{D,pulse}	1300	А
Avalanche energy, single pulse		E _{AS}	1750	mJ
Power dissipation T _C =25°C		P _D	430	W
Operating junction and storage temperature range		T _J , T _{stg}	-55 to 150	℃



Thermal Characteristics

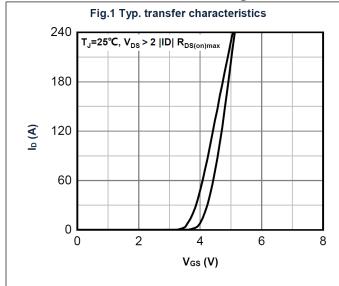
Parameter		Symbol	Max.	Uni t
Thermal resistance, junction-to-case	Steady state	Rejc	0.3	
Thermal resistance, junction-to-ambient	Steady state	Reja	40	°C/W

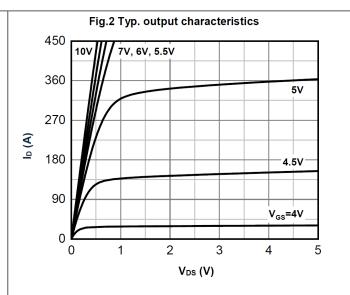
Electrical Characteristics at Tj=25°C unless otherwise specified

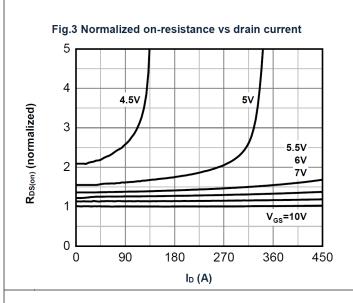
Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions	
Static							
Drain to source breakdown voltage	V _{(BR)DSS}	100			V	V _{GS} = 0, I _D = 250 μA	
Gate-source threshold voltage	V _G s(th)	2.2	3	3.8	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Gate-body leakage	$I_{\rm GSS}$			±100	nA	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	
Zero gate voltage drain current	I _{DSS}			1	μΑ	V _{DS} = 80 V, V _{GS} = 0 V	
Drain-source on-resistance	Ros(on)		1.1	1.5	mΩ	V _{GS} = 10 V, I _D = 10 A	
Drain-source on-resistance	Ros(on)		-	-	mΩ	V _{GS} = 4.5 V, I _D = 30 A	
Forward transconductance	gfs		49		S	V _{DS} = 5 V, I _D = 30 A	
Gate resistance	Rg		0.9		Ω	f=1MHz	
		Ga	te Char	ge			
Total gate charge	Qg		258	362			
Gate-source charge	Qgs		59	83	nC	$V_{DS} = 50 \text{ V}, I_D = 33 \text{ A}, V_{GS} = 10 \text{ V}$	
Gate-drain charge	Qgd		69	97			
Dynamic							
Turn-on delay time	$t_{d(on)}$		64	128			
Rise time	t _r		61	122		$V_{DS} = 50 \text{ V}, I_{D} = 33 \text{ A}, V_{GS} = 10 \text{ V},$	
Turn-off delay time	$t_{\text{d(off)}} \\$		221	442	ns	$R_{GEN} = 6 \Omega$	
Fall time	t_f		104	208	110		
Input capacitance	C_{iss}		15650	21910			
Output capacitance	C_{oss}		2100	2940		V _{DS} =25 V, V _{GS} = 0 V, f = 1MHz	
Reverse transfer capacitance	C_{rss}		45	90	pF		
Body Diode							
Diode forward voltage	V _{SD}		0.8	1.1	V	V _{GS} = 0 V, I _F = 33 A	
Reverse recovery time	t _{rr}		116	209	ns	V_R = 50 V, I_S =33 A, di/dt = 100	
Reverse recovery charge	Qrr		405	729	nC	A/μs	

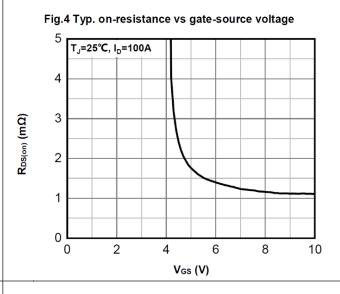


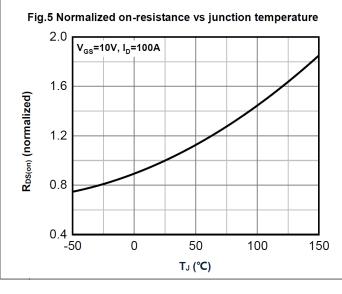
Electrical Characteristics Diagrams

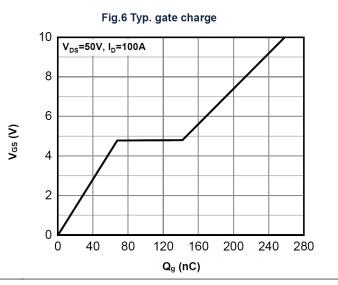




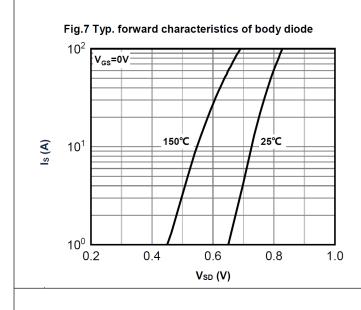


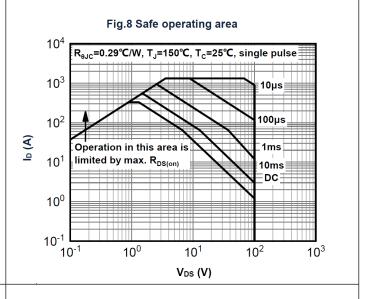


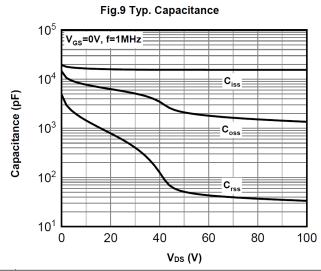


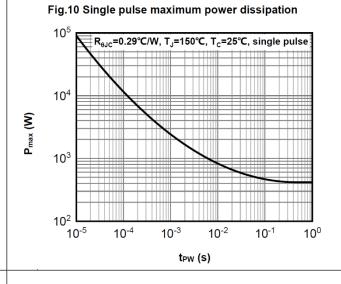


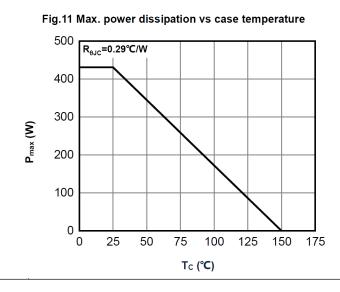


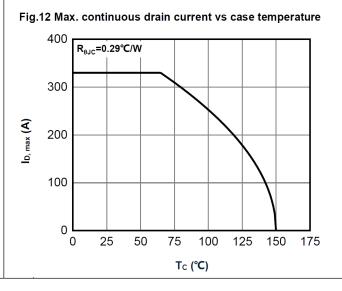




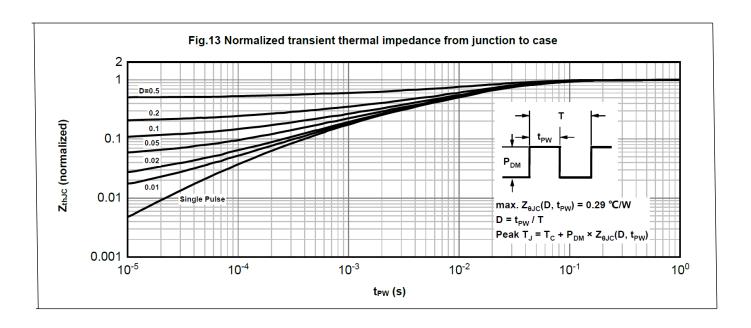






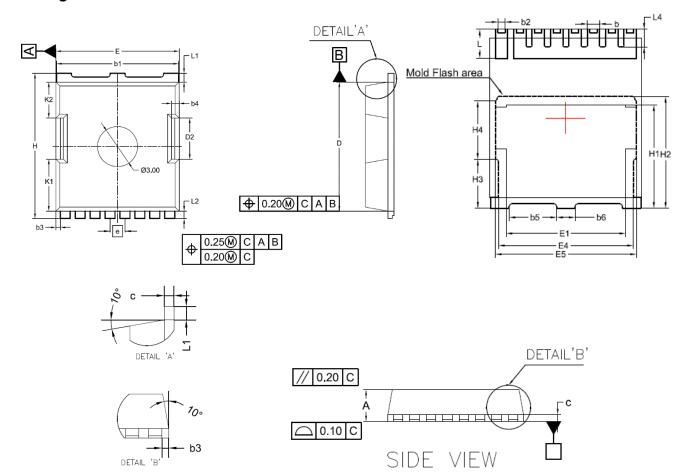








Package Outline Dimensions



SYMBOLS	DIMENSION IN MM			DIMENSION IN INCHES		
STIVIBULS	MIN	NOM	MAX	MIN	NOM	MAX
* A	2.200	2.300	2.400	0.087	0.091	0.094
С	0.492	0.500	0.508	0.019	0.020	0.020
* D	10.280	10.380	10.480	0.405	0.409	0.413
* E	9.800	9.900	10.000	0.386	0.390	0.394
e		1.20 BSC			0.047 BSC	
* H	11.580	11.680	11.780	0.456	0.460	0.464
H1	6.650	6.750	6.850	0.262	0.266	0.270
H2		7.300			0.287	
Н3		3.200			0.126	
H4	3.800			0.150		
K1	4.180			0.165		
K2	2.900			0.114		
* D2	3.300			0.130		
b	0.700	0.800	0.900	0.028	0.031	0.035
b1	9.700	9.800	9.900	0.382	0.386	0.390
b2	0.420	0.460	0.500	0.017	0.018	0.020
b3		0.350		0.014		
b4		0.600		0.024		
b5		3.100		0.122		
b6		1.200		0.047		
L	1.700	1.900	2.100	0.067	0.075	0.083
L1		0.700		0.028		
L2		0.600		0.024		
L4	1.050	1.150	1.250	0.041	0.045	0.049
L5	0.500	0.600	0.700	0.020	0.024	0.028
E1	7.800			0.31		
E4		8.800		0.35		
E5	9.200			0.36		



Legal Disclaimer

The information given in this document shall be for illustrative purposes only and shall in no event be regarded as a guarantee of conditions or characteristics. Existar Technologies reserves the right to change any information herein. With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Existar Technologies or its affiliates hereby make no representation or warranty of any kind, expressed or implied, as to any information provided hereunder, including without limitation as to the accuracy, completeness or non-infringement of intellectual property rights of any third party, and they assume no liability for the consequences of use of such information. In addition, any information given in this document is subject to customer's compliance with its obligations stated herein and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Existar Technologies in customer's applications. The information contained herein is exclusively intended for technically trained staff. No license is granted by implication under any patent right, copyright, mask work right, or other intellectual property right. It is customer's sole responsibility to evaluate the suitability of the product for the intended application and the completeness of the product information given herein with respect to such application. In no event shall Existar Technologies or its affiliates be liable to any party for any direct, indirect, special, punitive, incidental or consequential damages of any nature whatsoever, including but not limited to loss of profits and loss of goodwill, whether or not such damages are based on tort or negligence, warranty, breach of contract or any other legal theory.